# **BLC9G21LS-60AV**

# Power LDMOS transistor

**AMPLEON** 

Rev. 1 — 6 July 2017

Product data sheet

# 1. Product profile

### 1.1 General description

60 W LDMOS packaged asymmetric Doherty power transistor for base station applications at frequencies from 1805 MHz to 2200 MHz.

Table 1. Typical performance

Typical RF performance at  $T_{case}$  = 25 °C in the Doherty demo board.

Test signal	f	V <sub>DS</sub>	P <sub>L(AV)</sub>	G <sub>p</sub>	η <sub>D</sub>	ACPR
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
1-carrier W-CDMA	1930 to 1990	28	2.5	17.5	30	_39 <mark>[1]</mark>

<sup>[1]</sup> Test signal: 3GPP test model 1; 64 DPCH; PAR = 7.2 dB at 0.01% probability on CCDF per carrier.

#### 1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Asymmetric design to achieve optimum efficiency across the band
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

## 1.3 Applications

 RF power amplifiers for base stations and multi carrier applications in the 1805 MHz to 2200 MHz frequency range

# 2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
1	drain1 (main)			
2	drain2 (peak)			1, 5
3	gate1 (main)			3_
4	gate2 (peak)		7	7
5	video decoupling (main)			4
6	video decoupling (peak)		3 4	2, 6
7	source	[1]		aaa-007731

<sup>[1]</sup> Connected to flange.

# 3. Ordering information

Table 3. Ordering information

Type number	Packag	ackage				
	Name	Description	Version			
BLC9G21LS-60AV	-	air cavity plastic earless flanged package; 6 leads	SOT1275-1			

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	65	V
$V_{GS}$	gate-source voltage		-0.5	+13	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

<sup>[1]</sup> Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

# 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-c)</sub>	thermal resistance from junction to case	T <sub>case</sub> = 80 °C		
		P <sub>L</sub> = 2.5 W	0.92	K/W
		P <sub>L</sub> = 9.5 W	0.97	K/W

## 6. Characteristics

Table 6. DC characteristics

 $T_i$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main dev	ice		<b>"</b>	1		
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.2 \text{ mA}$	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 20 mA	1.5	2	2.5	V
$V_{GSq}$	gate-source quiescent voltage	V <sub>DS</sub> = 28 V; I <sub>D</sub> = 100 mA	1.7	2.2	2.7	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 32 V	-	-	1.4	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	4	-	Α
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V	-	-	140	nA
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 1.0 A	-	1.5	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 0.7 \text{ A}$	-	624	1135	mΩ
Peak dev	rice		1			
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.3 \text{ mA}$	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 30 mA	1.5	2	2.5	V
$V_{GSq}$	gate-source quiescent voltage	V <sub>DS</sub> = 28 V; I <sub>D</sub> = 150 mA	1.7	2.2	2.7	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 32 V	-	-	1.4	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	6	-	Α
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V	-	-	140	nA
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 1.5 A	-	2.2	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 1.05 \text{ A}$	-	420	760	mΩ

#### Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 100 mA (main);  $V_{GS(amp)peak}$  = 0.8 V;  $T_{case}$  = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 1930 MHz to 1990 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P <sub>L(AV)</sub> = 2.5 W	16.3	17.5	-	dB
RLin	input return loss	P <sub>L(AV)</sub> = 2.5 W	-	-10	<b>-7</b>	dB
$\eta_{D}$	drain efficiency	P <sub>L(AV)</sub> = 2.5 W	26	30	-	%
ACPR	adjacent channel power ratio	P <sub>L(AV)</sub> = 2.5 W	-	-39	-34	dBc

#### Table 8. RF characteristics

Test signal: pulsed CW;  $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 100 mA (main);  $V_{GS(amp)peak}$  = 0.8 V;  $T_{case}$  = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 1930 MHz to 1990 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$P_{L(M)}$	peak output power		53	60	-	W

# 7. Test information

# 7.1 Ruggedness in Doherty operation

The BLC9G21LS-60AV is capable of withstanding a load mismatch corresponding to a VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS}$  = 28 V;  $I_{Dq}$  = 100 mA (main);  $V_{GS(amp)peak}$  = 0.8 V;  $P_L$  = 38 W (CW);  $f_1$  = 1805 MHz;  $f_2$  = 1930 MHz.

# 7.2 Impedance information

Table 9. Typical impedance of main device Measured load-pull data of main device;  $I_{Da} = 100 \text{ mA (main)}$ ;  $V_{DS} = 28 \text{ V}$ .

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [2]	G <sub>p</sub> [2]
(MHz)	<b>(</b> Ω <b>)</b>	<b>(</b> Ω <b>)</b>	(W)	(%)	(dB)
Maximum	power load	,	'		
1805	2.4 – j6.9	12.0 – j9.4	30.7	63.9	16.4
1842	2.3 – j7.1	12.0 – j9.4	30.2	63.5	16.5
1880	2.6 – j7.9	11.0 – j8.0	29.3	61.2	16.2
1930	2.6 - j9.3	12.0 – j9.4	27.8	60.1	16.6
1960	3.2 – j9.0	12.0 – j9.4	28.4	60.6	16.5
1990	3.4 – j9.6	12.0 – j9.4	27.4	59.1	16.6
2110	4.7 – j15.9	9.7 – j8.8	29.2	60.6	18.0
2140	6.7 – j15.3	9.7 – j8.8	28.1	58.9	18.0
2170	5.3 – j19.6	9.7 – j8.8	29.1	61.7	18.3
Maximum	drain efficiency loa	ıd	·		
1805	2.4 – j6.9	23.6 - j0.0	20.5	73.3	18.2
1842	2.3 – j7.1	20.0 - j0.0	21.7	73.0	18.0
1880	2.6 - j7.9	19.6 – j3.1	18.9	71.5	18.4
1930	2.6 - j9.3	17.0 – j2.4	18.5	67.9	18.5
1960	3.2 – j9.0	14.8 – j2.0	19.7	69.3	18.3
1990	3.4 – j9.6	15.0 – j0.0	20.0	66.4	18.3
2110	4.7 – j15.9	13.0 – j1.6	17.7	69.4	20.6
2140	6.7 – j15.3	11.2 – j2.7	21.9	66.2	19.5
2170	5.3 – j19.6	11.6 – j1.4	20.7	70.6	20.5

<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in Figure 1.

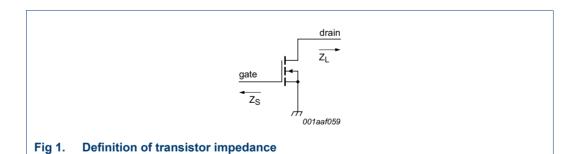
<sup>[2]</sup> at 3 dB gain compression.

Table 10. Typical impedance of peak device

Measured load-pull data of peak device;  $I_{Dq}$  = 150 mA (peak);  $V_{DS}$  = 28 V.

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [2]	G <sub>p</sub> [2]
(MHz)	<b>(</b> Ω <b>)</b>	<b>(</b> Ω <b>)</b>	(W)	(%)	(dB)
Maximum p	ower load	"	'		1
1805	2.2 – j6.6	6.5 – j7.7	46.2	63.4	15.9
1842	1.8 – j6.9	6.5 – j7.7	44.8	63.0	16.4
1880	2.5 – j7.0	6.5 – j7.7	43.0	61.4	16.2
1930	2.5 – j7.9	6.5 – j7.7	41.8	60.9	16.4
1960	2.8 – j8.0	6.9 – j8.6	41.9	60.1	16.3
1990	2.8 – j8.4	6.9 – j8.6	43.8	62.4	16.3
2110	5.1 – j12.6	5.7 – j8.0	43.8	62.5	17.7
2140	4.9 – j12.6	5.9 – j8.9	42.2	59.0	17.6
2170	5.8 – j14.8	5.9 – j8.9	43.1	60.9	17.8
Maximum d	rain efficiency loa	ad			<u>'</u>
1805	2.2 – j6.6	10.3 – j1.2	32.0	74.9	17.8
1842	1.8 – j6.9	9.2 – j1.0	31.1	74.5	18.1
1880	2.5 – j7.0	9.0 - j2.0	30.4	69.8	18.2
1930	2.5 – j7.9	7.3 – j1.5	28.6	69.6	18.3
1960	2.8 – j8.0	7.1 – j2.3	29.6	68.5	18.1
1990	2.8 – j8.4	7.3 – j1.5	28.6	72.7	18.8
2110	5.1 – j12.6	7.0 – j4.0	32.0	70.3	19.8
2140	4.9 – j12.6	6.0 – j4.1	30.4	67.8	19.7
2170	5.8 – j14.8	6.0 – j4.1	30.6	70.5	20.2

- [1] Z<sub>S</sub> and Z<sub>L</sub> defined in Figure 1.
- [2] at 3 dB gain compression.



# 7.3 Recommended impedances for Doherty design

Table 11. Typical impedance of main device at 1 : 1 load Measured load-pull data of main device;  $I_{Dq}$  = 100 mA (main);  $V_{DS}$  = 28 V.

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [3]	G <sub>p</sub> [3]
(MHz)	(Ω)	<b>(</b> Ω <b>)</b>	(W)	(%)	(dB)
1805	2.4 – j6.9	13.6 – j8.2	30.2	67.0	19.7
1842	2.3 – j7.1	13.6 – j8.2	29.4	66.6	19.9
1880	2.6 – j7.9	13.6 – j8.2	28.6	65.6	20.0
1930	2.6 – j9.3	13.6 – j8.2	26.8	62.8	20.1
1960	3.2 – j9.0	13.6 – j8.2	27.5	63.6	20.0
1990	3.4 – j9.6	12.2 – j6.9	26.6	61.9	19.9
2110	4.7 – j15.9	12.2 – j6.9	27.4	66.4	21.9
2140	6.7 – j15.3	10.1 – j6.8	27.5	62.6	21.5
2170	5.3 – j19.6	11.0 – j8.0	28.5	64.9	21.8

<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in Figure 1.

Table 12. Typical impedance of main device at 1 : 2.7 load Measured load-pull data of main device;  $I_{Dq} = 100 \text{ mA (main)}$ ;  $V_{DS} = 28 \text{ V}$ .

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [3]	G <sub>p</sub> [3]
(MHz)	(Ω)	<b>(</b> Ω <b>)</b>	(W)	(%)	(dB)
1805	2.4 – j6.9	23.6 - j0.0	20.5	73.3	21.2
1842	2.3 – j7.1	20.0 - j0.0	21.7	73.0	21.2
1880	2.6 – j7.9	19.6 – j3.1	18.9	71.5	21.4
1930	2.6 – j9.3	17.0 – j2.4	18.5	67.9	21.5
1960	3.2 – j9.0	14.8 – j2.0	19.7	69.3	21.3
1990	3.4 – j9.6	15.0 – j0.0	20.0	66.4	21.3
2110	4.7 – j15.9	13.0 – j1.6	17.7	69.4	23.6
2140	6.7 – j15.3	11.2 – j2.7	21.9	66.2	22.5
2170	5.3 – j19.6	11.6 – j1.4	20.7	70.6	23.5

<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in Figure 1.

<sup>[2]</sup> at 3 dB gain compression.

<sup>[3]</sup> at  $P_{L(AV)} = 34 \text{ dBm}$ .

<sup>[2]</sup> at 3 dB gain compression.

<sup>[3]</sup> at  $P_{L(AV)} = 34 \text{ dBm}$ .

### 7.4 Test circuit

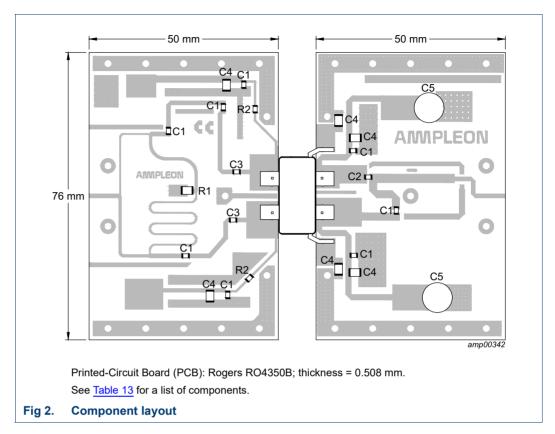


Table 13. List of components

See Figure 2 for component layout.

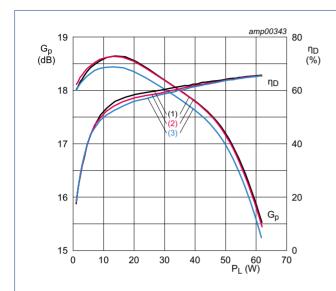
Component	Description	Value		Remarks
C1	multilayer ceramic chip capacitor	30 pF	[1]	
C2	multilayer ceramic chip capacitor	20 pF	[1]	
C3	multilayer ceramic chip capacitor	3.9 pF	[1]	
C4	multilayer ceramic chip capacitor	10 μF, 50 V	[2]	
C5	electrolytic capacitor	2200 μF, 63 V		
R1	resistor	50 Ω		SMD 2512
R2	resistor	5.1 Ω		SMD 0805

<sup>[1]</sup> American Technical Ceramics type 600F or capacitor of same quality.

<sup>[2]</sup> Murata or capacitor of same quality.

## 7.5 Graphical data

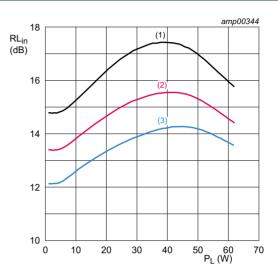
## 7.5.1 Pulsed CW



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 100 mA (main device);  $V_{GS(amp)peak}$  = 0.8 V.

- (1) f = 1930 MHz
- (2) f = 1960 MHz
- (3) f = 1990 MHz

Fig 3. Power gain and drain efficiency as function of output power; typical values

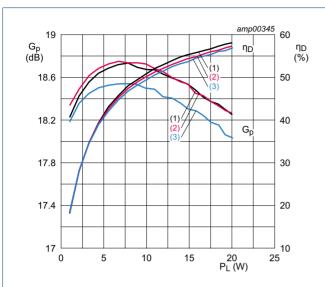


 $V_{DS}$  = 28 V;  $I_{Dq}$  = 100 mA (main device);  $V_{GS(amp)peak}$  = 0.8 V.

- (1) f = 1930 MHz
- (2) f = 1960 MHz
- (3) f = 1990 MHz

Fig 4. Input return loss as a function of output power; typical values

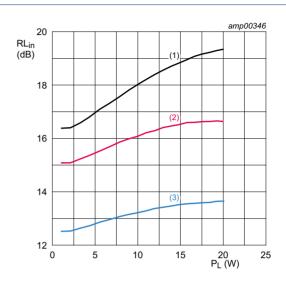
#### 7.5.2 1-Carrier W-CDMA



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 100 mA (main device);  $V_{GS(amp)peak}$  = 0.8 V.

- (1) f = 1930 MHz
- (2) f = 1960 MHz
- (3) f = 1990 MHz

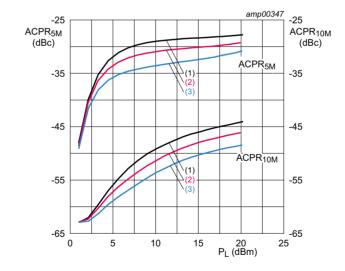
Fig 5. Power gain and drain efficiency as function of output power; typical values



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 100 mA (main device);  $V_{GS(amp)peak}$  = 0.8 V.

- (1) f = 1930 MHz
- (2) f = 1960 MHz
- (3) f = 1990 MHz

Fig 6. Input return loss as a function of output power; typical values

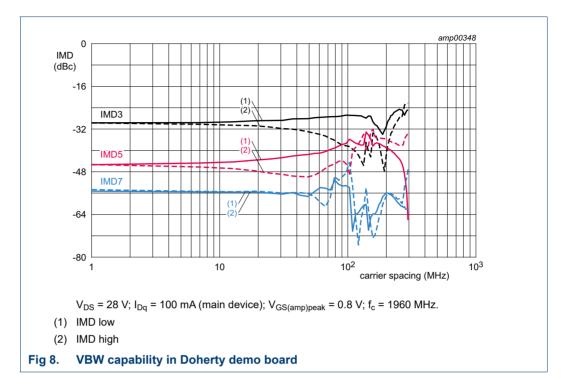


 $V_{DS}$  = 28 V;  $I_{Dq}$  = 100 mA (main device);  $V_{GS(amp)peak}$  = 0.8 V.

- (1) f = 1930 MHz
- (2) f = 1960 MHz
- (3) f = 1990 MHz

Fig 7. Adjacent channel power ratio (5 MHz) and adjacent channel power ratio (10 MHz) as function of output power; typical values

### 7.5.3 2-Tone VBW



# 8. Package outline

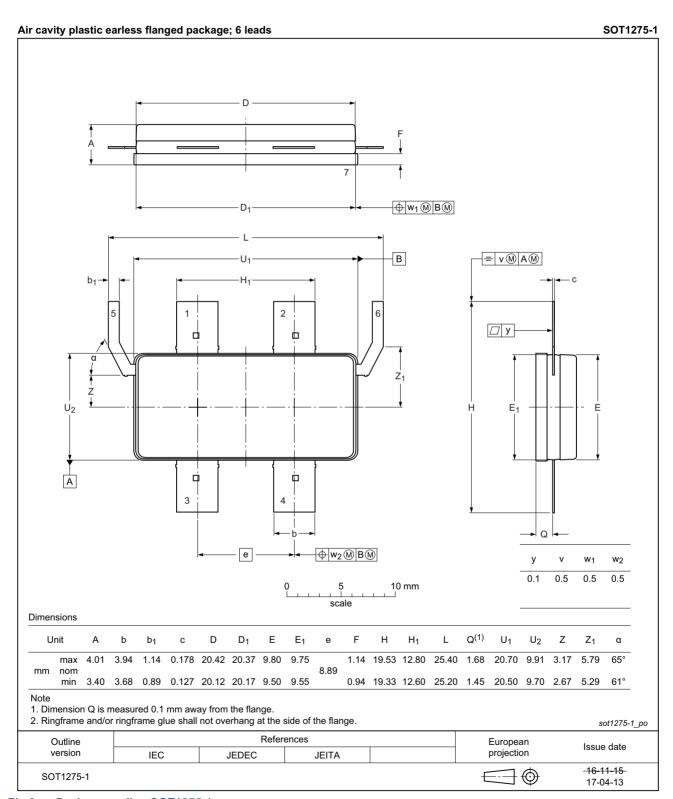


Fig 9. Package outline SOT1275-1

# 9. Handling information

#### **CAUTION**



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 14. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 750 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

## 10. Abbreviations

Table 15. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VBW	Video Bandwidth
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

# 11. Revision history

Table 16. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC9G21LS-60AV v.1	20170706	Product data sheet	-	-

# 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# **AMPLEON**

# **BLC9G21LS-60AV**

### **Power LDMOS transistor**

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